

CLAIMS

[Claim 1]

A composition for removing photoresist residue and/or polymer residue after dry etching or wet etching using a photoresist as a mask, the composition comprising saccharin and water, and the pH being no greater than 9.7.

[Claim 2]

The composition according to Claim 1, wherein it further comprises one or more types of substance selected from the group consisting of (A) a water-soluble solvent, (B) an acid, and (C) a dissociable nitrogen-containing compound.

[Claim 3]

The composition according to Claim 1 or 2, wherein the content of saccharin is at least 0.01 mass%.

[Claim 4]

A method for removing photoresist residue and/or polymer residue, the method employing the composition according to any one of Claims 1 to 3.

[Claim 5]

A method for producing a semiconductor circuit element having metal wiring,

the method comprising a step of removing photoresist residue and/or polymer residue remaining on a metal wiring-forming structure using the composition according to any one of Claims 1 to 3.